L Number	Hits	Search Text	DB	Time stamp
3	3	diffusion adj region near6 "between" near6 isolation adj region and (mos or mosfet).ti,ab,clm. and protection	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 13:58
4	0	(mos or mosfet).ti,ab,clm. and protection.ti,ab,clm. and separated near6 diffusion adj region near6 (isolation or field adj oxide or locos)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:00
5	0	("(mos or mosfet) near6 separated.ti,ab,clm.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:00
6	577	(mos or mosfet) near6 separated.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:01
7	24	((mos or mosfet) near6 separated.ti,ab,clm.) and protection near2 (device or circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:07
8	8	((mos or mosfet) near6 separated.ti,ab,clm.) and protection near2 (device or circuit) and (silicide or salicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:13
9	876	protection near2 (device or circuit) and (silicide or salicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:15
10	24	(fox or locos) near6 diode and (mos or mosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:22
11	8	(fox or locos) near6 diode and (mos or mosfet) and (silicide or salicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:32
12	0	array near2 lateral adj mosfet.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:33
13	0	array near2 lateral adj mosfet and mosfet.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:34
14	0	plurality near2 lateral adj mosfet.clm. and mosfet.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:35
15	407	plurality near2 mosfet.clm. and mosfet.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:35

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16	1	plurality near2 mosfet.clm. and mosfet.ti,ab,clm. and silicide and fox	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 14:54
17	2	silicide near6 advantage$3 near6 smooth	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 15:53
18	0	"on the same substrate" near6 plurality near6 mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 15:55
19	0	"insulated from other MOSFETs"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 15:55
20	18	tfo and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 17:44
21	2	jp-06224376$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 19:17
22	59	physical adj vapor adj deposition near2 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 20:12
23	5	866782.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 20:14
24	5	873370.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 20:17
25	2	jp-07273197$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 20:18
26	2	jp-07106570$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 20:18
27	2	jp-07094595$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 20:42
28	2	(("5744841") or ("5920774")).PN.	USPAT	2003/05/14 20:42
–	0	("salicide").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 13:36

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–	2475	salicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/05 17:08
–	431	salicide.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/05 17:08
–	229	(257/173).CCLS.	USPAT; US-PGPUB	2002/10/04 11:04
–	322	(257/339).CCLS.	USPAT; US-PGPUB	2002/10/04 11:04
–	725	(257/355).CCLS.	USPAT; US-PGPUB	2002/10/04 11:04
–	1186	((257/173).CCLS.) or ((257/339).CCLS.) or ((257/355).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 12:05
–	18	(((257/173).CCLS.) or ((257/339).CCLS.) or ((257/355).CCLS.)) and (mos or mosfet or nmos or nmosfet or pmos or pmosfet or cmos or cmosfet) and protect$3 and silicide and zener	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 13:58
–	18	(US-6307238-$ or US-6281527-$ or US-6268639-$ or US-6175139-$ or US-6121665-$ or US-5939767-$ or US-5910675-$ or US-5708288-$ or US-5683918-$ or US-5623387-$ or US-5543650-$ or US-5229633-$ or US-5166089-$ or US-5128730-$ or US-4509089-$ or US-6365941-$).did. or (US-20020096722-$ or US-20020030231-$).did.	USPAT; US-PGPUB	2002/10/04 13:29
–	132	(((257/173).CCLS.) or ((257/339).CCLS.) or ((257/355).CCLS.)) and (mos or mosfet or nmos or nmosfet or pmos or pmosfet or cmos or cmosfet) and zener	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 14:07
–	30	((257/288).CCLS.) and second near3 diffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 14:16
–	7	((257/288).CCLS.) and double-diffused	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 14:17
–	11	((257/288).CCLS.) and double adj diffused	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 14:18
–	788	(257/288).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 14:31
–	8	(US-6025628-$ or US-6307224-$ or US-4509089-$ or US-5166089-$ or US-6268639-$ or US-5623387-$).did. or (US-20020030231-$).did. or (JP-06204475-$).did.	USPAT; US-PGPUB; JPO	2002/10/04 19:04
–	8	((US-6025628-$ or US-6307224-$ or US-4509089-$ or US-5166089-$ or US-6268639-$ or US-5623387-$).did. or (US-20020030231-$).did. or (JP-06204475-$).did.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:18

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-	463	well same protect$3 same substrate same esd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:19
-	268	well same protect$3 same substrate same esd and 257/$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:19
-	112	(well same protect$3 same substrate same esd and 257/$6.ccls.) and well near4 protect$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:20
-	37	(well same protect$3 same substrate same esd and 257/$6.ccls.) and well near4 protect$3.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:21
-	12	(well same protect$3 same substrate same esd and 257/$6.ccls.) and well near4 protect$3.ti,ab,clm. and (mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/04 19:22
-	4	("4336489").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/06 10:34
-	2	jp-07273197$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 09:42
-	2	jp-07106570$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 09:33
-	2	jp-07094995$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 09:56
-	2	jp-07094595$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 09:47
-	1	jp-05136086$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 09:51
-	2	jp-03234062$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 09:54
-	2	jp-02271673$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 11:33
-	11	jp-07273197$-$.did. or jp-07106570$-$.did. or jp-07094995$-$.did. or jp-07094595$-$.did. or jp-05136086$-$.did. or jp-03234062$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 09:58

–	2012	((257/173) or (257/339) or (257/355)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 12:12
–	14	(((257/173) or (257/339) or (257/355)).CCLS.) and salicide and (MOS or MOSFET or CMOS or CMOSFET or NMOS or PMOS or NMOSFET or PMOSFET) and hot adj spot	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 11:38
–	9	(salicide and (MOS or MOSFET or CMOS or CMOSFET or NMOS or PMOS or NMOSFET or PMOSFET) and hot adj spot) not (((257/173) or (257/339) or (257/355)).CCLS.) and salicide and (MOS or MOSFET or CMOS or CMOSFET or NMOS or PMOS or NMOSFET or PMOSFET) and hot adj spot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 11:39
–	23	salicide and (MOS or MOSFET or CMOS or CMOSFET or NMOS or PMOS or NMOSFET or PMOSFET) and hot adj spot	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 11:42
–	1	(((257/173) or (257/339) or (257/355)).CCLS.) and salicide and (fox of field adj oxide or locos) and lateral adj bipolar adj transistor and (mos or mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or field adj effect adj transistor) and protection near3 (circuit or device) and zener	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 12:15
–	9	(((257/173) or (257/339) or (257/355)).CCLS.) and salicide and (mos or mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or field adj effect adj transistor or igfet or insulated adj gate adj field adj effect adj transistor) and protection near3 (circuit or device) and zener	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 12:22
–	14	(((257/173) or (257/339) or (257/355)).CCLS.) and salicide and (mos or mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or field adj effect adj transistor or igfet or insulated adj gate adj field adj effect adj transistor) and hot adj spot	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 12:24
–	12	((((257/173) or (257/339) or (257/355)).CCLS.) and salicide and (mos or mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or field adj effect adj transistor or igfet or insulated adj gate adj field adj effect adj transistor) and hot adj spot) not ((((257/173) or (257/339) or (257/355)).CCLS.) and salicide and (mos or mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or field adj effect adj transistor or igfet or insulated adj gate adj field adj effect adj transistor) and protection near3 (circuit or device) and zener)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 12:24